

MIL PROCESSING TEST PLAN FOR DLZ SERIES – H1 VERSIONS (Bidirectional)

TEST	CONDITION	MIL-STD-750 TEST METHOD
Internal Visual		2072
Storage	T _A = +150°C for 24 hours	1032
Temp Cycle	10 cycles, 15 minutes each extreme @ min/max rated temps	1051
Acceleration	20KG, Y1 axis, no hold time	2006
Electrical (Polarities A & B)	Reverse Current (I _R) @ rated V _{WM} Breakdown Voltage (V _(BR)) @ I _T	4016 4022
Pulse	10 pulses each polarity @ rated I _{pp} = 10A, t _p = 8 x 20μs	
Electrical	Reverse Current (I _R) @ rated V _{WM} (Polarities A & B)	4016
Burn-In(HTRB)	T _A = +125°C @ rated V _{WM} for 80 hours (Polarity A)	1038
Electrical (Polarity A)	Reverse Current (I _R) @ rated V _{WM} , D-I _R = 100% or 20% of Group A limit, whichever is greater	4016
Burn-In(HTRB)	T _A = +125°C @ rated V _{WM} for 80 hours (Polarity B)	1038
Electrical	Reverse Current (I _R) @ rated V _{WM} , D-I _R = 100% or 20% of Group A limit, whichever is greater (Polarity B)	4016
	Breakdown Voltage (V _(BR)) @ I _T , D-V _(BR) ±2% from initial reading (Polarities A & B)	4022
	Reverse Current (I _R) @ rated V _{WM} (Polarity A)	4016
Fine Leak	1 x 10 ⁻⁸ atmcc/sec	1071G/H
Gross Leak	T _A = +125°C, no bubbles	1071C/D
Marking		
Group A	Reverse Current (I _R) @ rated V _{WM}	4016
	Breakdown Voltage (V _(BR)) @ I _T	4022
	Clamping Voltage (V _C) @ I _{pp} , t _p = 8 x 20μs	
	Capacitance @ 0V	4001